

InGaAs PIN Photodiode

Model: OPR2000-IGA26-O

Features

- Low voltage operation
- Enhance InGaAs PIN: 1000 to 2600nm
- Isolated type is also available



Applications

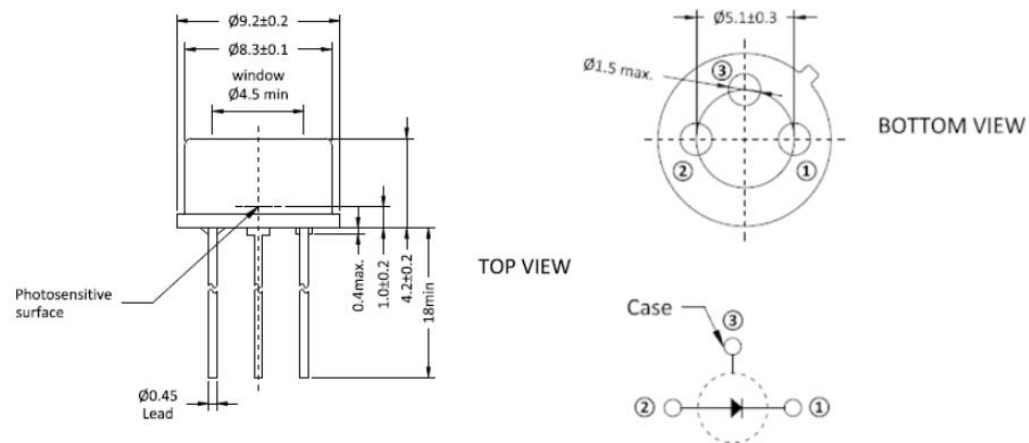
- Optical Instrumentation
- NIR Sensing
- Laser Power Measurement
- Power meters

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

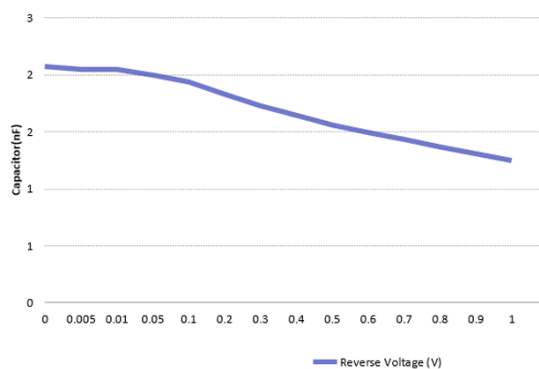
Parameter	Symbol	Value			Unit	Test conditions
		Min.	Typ.	Max.		
Chip Size	s	3000*3000*175			μm	
Active area	A	$\Phi 2000$			μm	
Forward current	I_F	10			mA	
Reverse current	I_R	10			mA	
Dark current	I_D			13 72.5	μA	$V_R=0\text{V}$ $V_R=1\text{V}$
Cut frequency	f_C		45		MHz	$V_R=0\text{V}$; $R_L=50\Omega$
Reverse breakdown voltage	$V_{(BR)R}$			1	V	$I_R=10\mu\text{A}$; $E_V=0\text{lX}$
Junction Capacitance	C_j		2.07		nF	$V_R=0\text{V}$; $f=1\text{MHz}$
Photo sensitivity	S_R	0.97			A/W	$V_R=0.1\text{V}$; $\lambda=2000\text{nm}$
Spectral Application Range	λ_{range}	1000		2600	nm	
Spectral Response-Peak	λ_p		2500		nm	
Shunt resistance	R_{sh}		8		K Ω	$V_R=10\text{mV}$
Angular Resp 50% resp pt	$\theta_{1/2}$		± 35		Degrees	λ
Noise Equivalent Power	NEP		5.16×10^{-10}		W/Hz ^{1/2}	$\lambda=2.5\mu\text{m}$

Block Diagram and Pin description

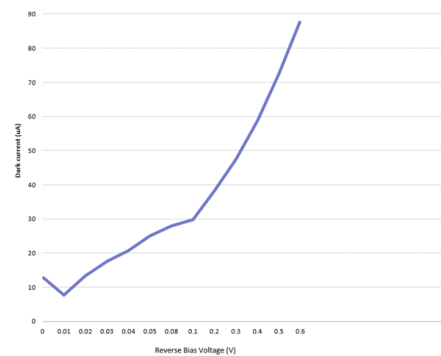
Note: All dimension are in millimeters.



Capacitance vs. UR



Dark current vs. UR



Spectral response

